

# BC856BM3T5G

Preferred Devices

## General Purpose Transistor

### PNP Silicon

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-723 which is designed for low power surface mount applications.

- This is a Pb-Free Device

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-65	V
Collector-Base Voltage	$V_{CBO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current - Continuous	$I_C$	-100	mA

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	265	mW
		2.1	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	470	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	640	mW
		5.1	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	195	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

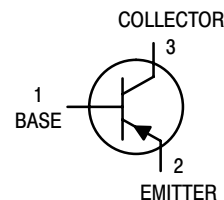
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

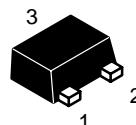


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#### MARKING DIAGRAM



SOT-723  
CASE 631AA  
STYLE 1



3B = Specific Device Code  
M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
BC856BM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# BC856BM3T5G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –10 mA)	V <sub>(BR)CEO</sub>	–65	–	–	V
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –10 μA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	–80	–	–	V
Collector–Base Breakdown Voltage (I <sub>C</sub> = –10 μA)	V <sub>(BR)CBO</sub>	–80	–	–	V
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –1.0 μA)	V <sub>(BR)EBO</sub>	–5.0	–	–	V
Collector Cutoff Current (V <sub>CB</sub> = –30 V) (V <sub>CB</sub> = –30 V, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	–	–	–15 –4.0	nA μA

### ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = –10 μA, V <sub>CE</sub> = –5.0 V) (I <sub>C</sub> = –2.0 mA, V <sub>CE</sub> = –5.0 V)	h <sub>FE</sub>	– 220	150 290	– 475	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = –10 mA, I <sub>B</sub> = –0.5 mA) (I <sub>C</sub> = –100 mA, I <sub>B</sub> = –5.0 mA)	V <sub>CE(sat)</sub>	– –	– –	–0.3 –0.65	V
Base–Emitter Saturation Voltage (I <sub>C</sub> = –10 mA, I <sub>B</sub> = –0.5 mA) (I <sub>C</sub> = –100 mA, I <sub>B</sub> = –5.0 mA)	V <sub>BE(sat)</sub>	– –	–0.7 –0.9	– –	V
Base–Emitter Voltage (I <sub>C</sub> = –2.0 mA, V <sub>CE</sub> = –5.0 V) (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 V)	V <sub>BE(on)</sub>	–0.6 –	– –	–0.75 –0.82	mV

### SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	–	–	MHz
Output Capacitance (V <sub>CB</sub> = –10 V, f = 1.0 MHz)	C <sub>obo</sub>	–	–	4.5	pF
Noise Figure (I <sub>C</sub> = –0.2 mA, V <sub>CE</sub> = –5.0 Vdc, R <sub>S</sub> = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

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## TYPICAL CHARACTERISTICS

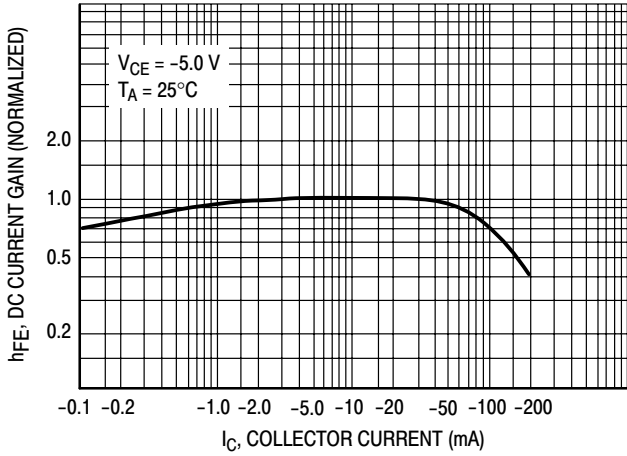


Figure 1. DC Current Gain

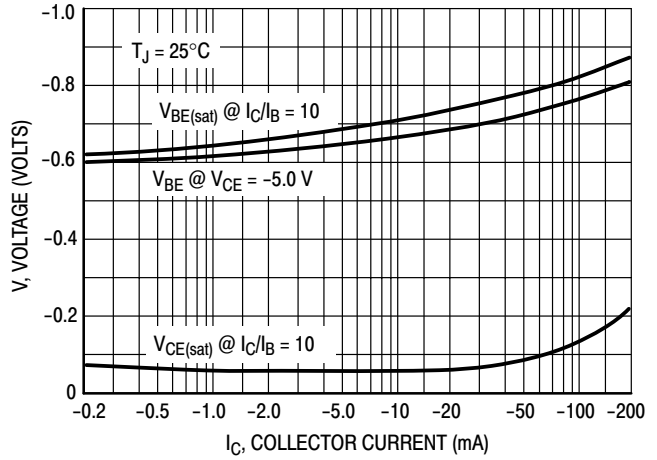


Figure 2. "On" Voltage

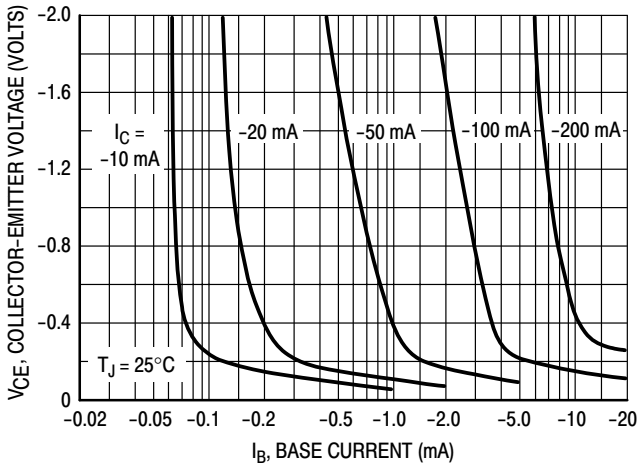


Figure 3. Collector Saturation Region

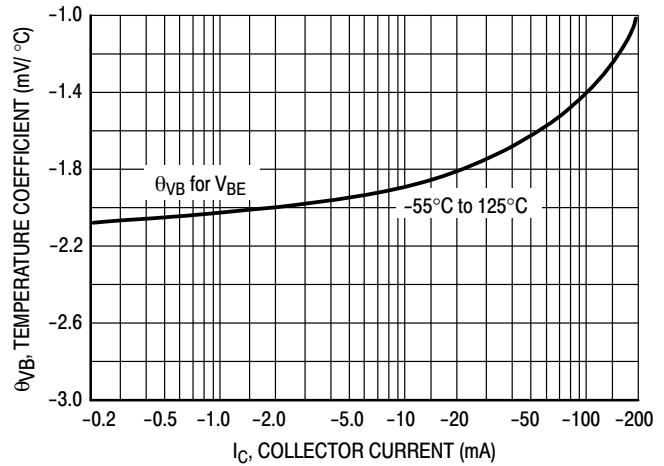


Figure 4. Base-Emitter Temperature Coefficient

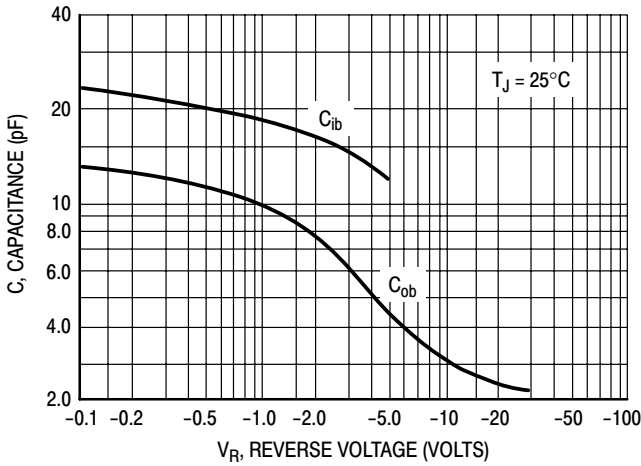


Figure 5. Capacitance

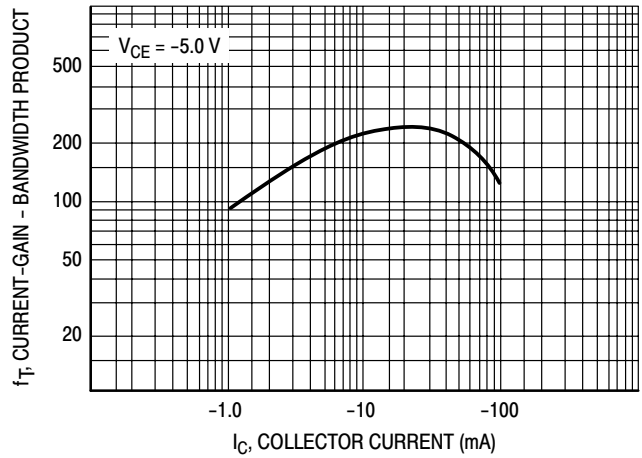
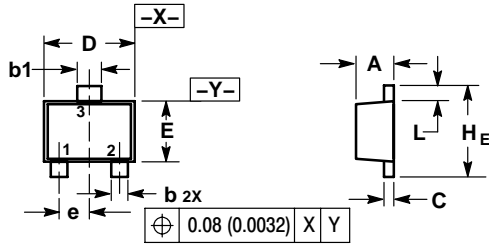


Figure 6. Current-Gain - Bandwidth Product

# BC856BM3T5G

## PACKAGE DIMENSIONS

SOT-723  
CASE 631AA-01  
ISSUE B



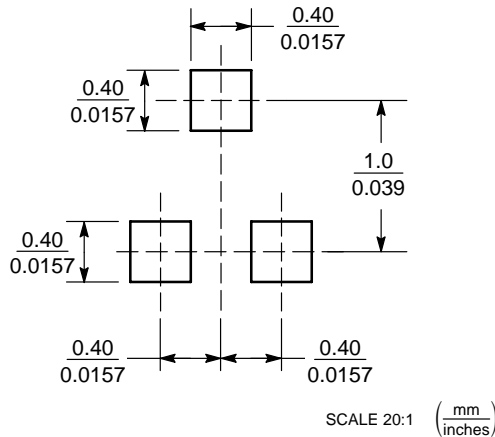
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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